# **CNA1302K** (ON1004)

## Photo Interrupter

For contactless SW and object detection

#### Overview

CNA1302K is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

#### Features

• Ultraminiature: 4.2 mm × 5.0 mm (height: 5.2 mm)

• Fast response:  $t_r$ ,  $t_f = 35 \mu s$  (typ.)

• Highly precise position detection: 0.15 mm

• Gap width: 2.0 mm

### ■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Symbol Rating		
	Power dissipation *1	$P_{\mathrm{D}}$	75	mW
Input (Light emitting diode)	Forward current	$I_{\mathrm{F}}$	50	mA
	Reverse voltage V <sub>R</sub>		6	V
Output (Photo transistor)	Collector-emitter voltage (Base open) V <sub>CEO</sub>		35	V
	Emitter-collector voltage (Base open)	V <sub>ECO</sub>	V <sub>ECO</sub> 6	
	Collector current	$I_{C}$	20	mA
	Collector power dissipation *2	$P_{\rm C}$	75	mW
Operating ambient temp	T <sub>opr</sub>	-25 to +85	°C	
Storage temperature	T <sub>stg</sub>	-40 to +100	°C	

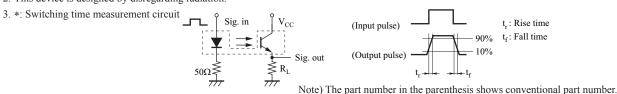
Note) \*1: Input power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C

### ■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

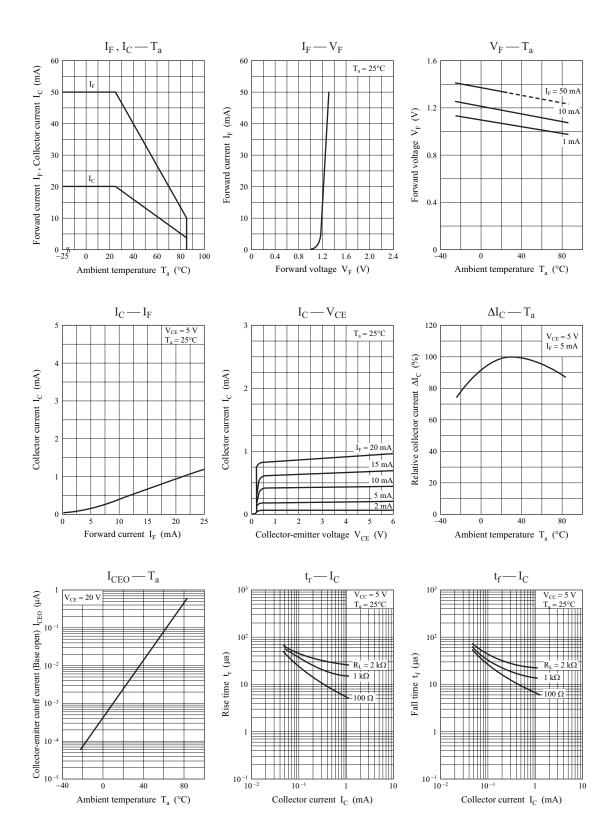
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	$I_R$	$V_R = 3 V$			10	μΑ
	Forward voltage	V <sub>F</sub>	$I_F = 20 \text{ mA}$		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 20 \text{ V}$			100	nA
Transfer characteristics	Collector current	$I_{C}$	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	40		400	μΑ
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_F = 10 \text{ mA}, I_C = 40 \mu\text{A}$			0.4	V
	Rise time *	t <sub>r</sub>	$V_{CC} = 5 \text{ V}, I_C = 0.1 \text{ mA},$		35		μs
	Fall time *	$t_{\mathrm{f}}$	$R_{\rm L} = 1000\Omega$		35		μs

Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.

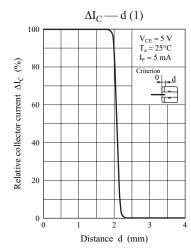


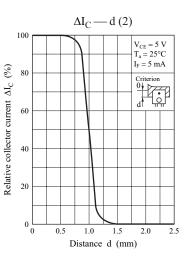
<sup>\*2:</sup> Output power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C



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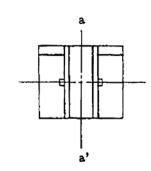
Panasonic CNA1302K

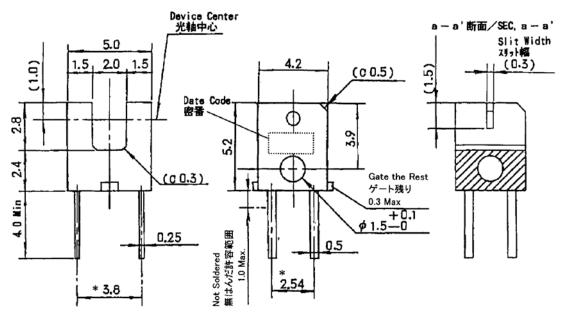


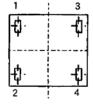


#### ■ Package (Unit: mm)

## LSMSIN4S0005







- (注 1)(Note1) \* リード根元寸法とします/ \* Indicates root dimensions of lead.
- (注 2)(Note2)指示無き寸法公差は±0.2/Not appointment tolerance :±0.2
- (注 3)(Note3)パリ寸法は 0.15 Max./Barri measure : 0.15 Max.
- (注 4) 上記寸法は、バリ・ゲート残り等を含んでおりません

(Note4)An aforementioned dimension doesn't include projects and gate the rest remainder.

(注 5) 密番は、目視又は顕微鏡に於いて解読できる事

(Note5)What a date code sees an attention and can decode in a microscope.

- Pin name
  - 1: Anode
  - 2: Cathode
  - 3: Collector
  - 4: Emitter

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